TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

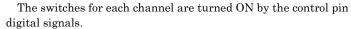
TC7MZ4051FK,TC7MZ4052FK,TC7MZ4053FK

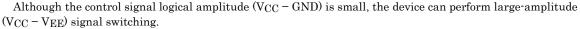
TC7MZ4051FK 8-Channel Analog Multiplexer/Demultiplexer TC7MZ4052FK Dual 4-Channel Analog Multiplexer/Demultiplexer

TC7MZ4053FK Triple 2-Channel Analog Multiplexer/Demultiplexer

The TC7MZ4051/4052/4053FK are high-speed, low-voltage drive analog multiplexer/demultiplexers using silicon gate CMOS technology. In 3 V and 5 V systems these can achieve high-speed operation with the low power dissipation that is a feature of CMOS.

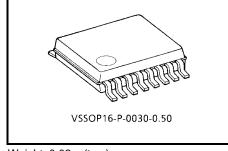
The TC7MZ4051/4052/4053FK offer analog/digital signal selection as well as mixed signals. The 4051 has an 8-channel configuration, the 4052 has an 4-channel \times 2 configuration, and the 4053 has a 2-channel \times 3 configuration.





For example, if $V_{CC} = 3 \text{ V}$, GND = 0 V, and $V_{EE} = -3 \text{ V}$, signals between -3 V and +3 V can be switched from the logical circuit using a single 3 V power supply.

All input pins are equipped with a newly developed input protection circuit that avoids the need for a diode on the plus side (forward side from the input to the VCC). As a result, for example, 5 V signals can be permitted on the inputs even when the power supply voltage to the circuits is off. As a result of this input power protection, the TC7MZ4051/4052/4053FK can be used in a variety of applications, including in the system which has two power supplies, and in battery backup circuits.



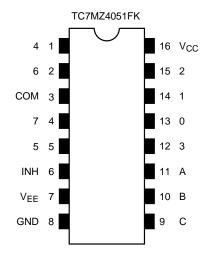
Weight: 0.02 g (typ.)

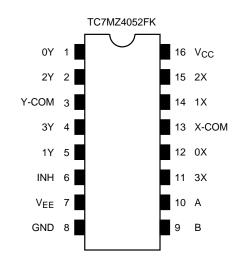
Features

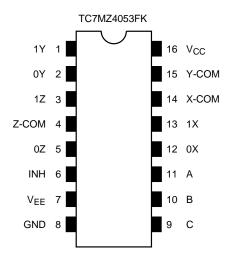
- Low ON resistance: $R_{on} = 22 \Omega \text{ (typ.)} \text{ (VCC VEE = 3 V)}$ $R_{on} = 15 \Omega \text{ (typ.)} \text{ (VCC - VEE = 6 V)}$
- High speed: $t_{pd} = 3 \text{ ns (typ.)} (V_{CC} = 3.0 \text{ V})$
- Low power dissipation: I_{CC} = 4 μA (max) (Ta = 25°C)
- Input level: $V_{IL} = 0.8 \text{ V (max)} (V_{CC} = 3 \text{ V})$ $V_{IH} = 2.0 \text{ V (min)} (V_{CC} = 3 \text{ V})$
- Power down protection is provided on all control inputs
- Pin and function compatible with 74HC4051/4052/4053



Pin Assignment (top view)







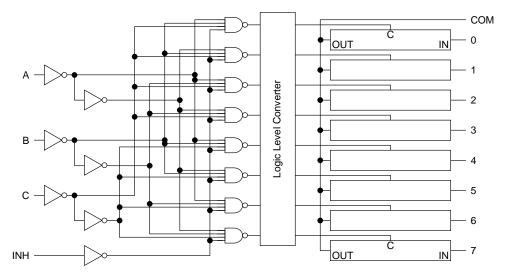
Truth Table

	Contro	I Inputs		"ON" Channel				
Inhibit	C*	В	Α	MZ4051FK	MZ4053FK			
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z		
L	L	L	Н	1	1X, 1Y	1X, 0Y, 0Z		
L	L	Н	L	2	2X, 2Y	0X, 1Y, 0Z		
L	L	Н	Н	3	3X, 3Y	1X, 1Y, 0Z		
L	Н	L	L	4	_	0X, 0Y, 1Z		
L	Н	L	Н	5	_	1X, 0Y, 1Z		
L	Н	Н	L	6	_	0X, 1Y, 1Z		
L	Н	Н	Н	7	_	1X, 1Y, 1Z		
Н	Х	Х	Х	None	None	None		

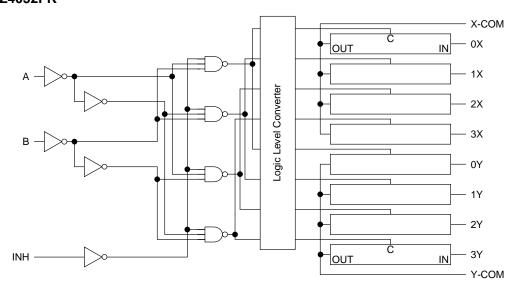
X: Don't care, *: Except MZ4052FK

System Diagram

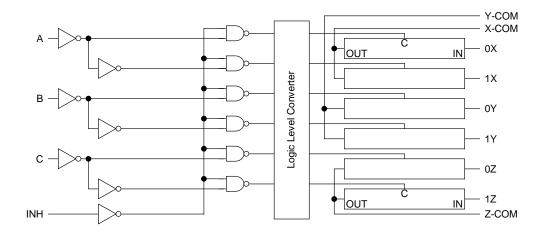
TC7MZ4051FK



TC7MZ4052FK



TC7MZ4053FK





Absolute Maximum Ratings

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	-0.5~7.0	V	
Fower supply voltage	V _{CC} ~V _{EE}	-0.5~7.0	v	
Control input voltage	V _{IN}	-0.5~7.0	V	
Switch I/O voltage	V _{I/O}	V _{EE} - 0.5~V _{CC} + 0.5	V	
Input diode current	I _{IK}	-20	mA	
I/O diode current	I _{IOK}	±20	mA	
Switch through current	Ι _Τ	±25	mA	
DC V _{CC} or ground current	Icc	±50	mA	
Power dissipation	P _D	180	mW	
Storage temperature	T _{stg}	-65~150	°C	

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit	
	V _{CC}	2~6		
Power supply voltage	V _{EE}	-4~0	V	
	V _{CC} ~V _{EE}	2~6		
Input voltage	V _{IN}	0~6.0	V	
Switch I/O voltage	V _{I/O}	VEE~VCC	V	
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	$0 \sim 100 \; (V_{CC} = 3.3 \pm 0.3 \; V)$	ns/V	
input use and rail time	ul/uv	0~20 (V _{CC} = 5 ± 0.5 V)	115/V	



Electrical Characteristics

DC Electrical Characteristics

Characteristics		Symbol	Test Condition			Ta = 25°C			Ta = -4	Ta = -40~85°C	
		Gymbor	rest condition	V _{EE} (V)	V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit
					2.0	1.5	_	_	1.5	_	
	High-level	V _{IH}			3.0	2.0	_	_	2.0	_	
	i ligit-level	V IH	_		4.5	3.15	_	_	3.15	_	
Input voltage					6.0	4.2		_	4.2	_	V
input voltage					2.0		_	0.5	_	0.5	v
	Low-level	VIL			3.0			0.8	_	0.8	
	Low-level	V IL	_		4.5		_	1.35	_	1.35	
					6.0		_	1.8	_	1.8	
ON resistance			Var. Va. or Var.	GND	2.0		200	_	_	_	
		R _{ON}	$\begin{split} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{I/O} = V_{CC} \text{ to } V_{EE} \\ &I_{I/O} = 2 \text{ mA} \end{split}$	GND	3.0		45	86	_	108	Ω
				GND	4.5		24	37		46	
				-3.0	3.0		17	26	_	33	
			$\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{I/O} = V_{CC} \text{ or } V_{EE} \\ &I_{I/O} = 2 \text{ mA} \end{aligned}$	GND	2.0		28	73		84	
				GND	3.0		22	38	_	44	
				GND	4.5		17	27		31	
				-3.0	3.0		15	24	_	28	
		ΔR _{ON}	$\begin{aligned} & V_{IN} = V_{IL} \text{ or } V_{IH} \\ & V_{I/O} = V_{CC} \text{ to } V_{EE} \\ & I_{I/O} = 2 \text{ mA} \end{aligned}$	GND	2.0	-	10	25		35	Ω
Difference of O resistance betw				GND	3.0		5	15	_	20	
switches	iccii			GND	4.5		5	13		18	
				-3.0	3.0		5	10	_	15	
Input/Output lea	akage		$V_{OS} = V_{CC}$ or GND	GND	3.0			±0.25		±2.5	
current (switch OFF)			$V_{IS} = GND \text{ to } V_{CC}$ $V_{IN} = V_{IL} \text{ or } V_{IH}$	-3.0	3.0	_	_	±0.5	_	±5.0	μА
Input/Output leakage current (switch ON, output open)		I _{IN}	$V_{OS} = V_{CC}$ or GND	GND	3.0		_	±0.25	_	±2.5	μА
			$V_{IN} = V_{IL}$ or V_{IH}	-3.0	3.0	_	_	±0.5	_	±5.0	
Control input current		I _{IN}	$V_{IN} = V_{CC}$ or GND	GND	6.0	_	_	±0.1	_	±0.1	μА
Quiescent supply current			V V 0ND	GND	3.0	_		4.0	_	40.0	
		Icc	$V_{IN} = V_{CC}$ or GND	-3.0	3.0	_		8.0	_	80.0	μΑ



AC Electrical Characteristics ($C_L = 50 \text{ pF}$, Input: $t_r = t_f = 3 \text{ ns}$, GND = 0 V)

Characteristics	Symbol	Symbol Test Condition					Га = 25°C		Ta = -40~85°C		Unit
Characteristics	Symbol			V _{EE} (V)	V _{CC} (V)	Min	Тур.	Max	Min	Max	OTIIC
		All types		GND	2.0	_	3.2	6.0	_	6.9	
Phase difference between	φI/O			GND	3.0	_	1.8	3.0	_	3.5	ns
input and output	ψί/Ο			GND	4.5		1.3	1.8	_	2.1	113
				-3.0	3.0		1.1	1.3	_	1.5	
				GND	2.0		9.0	17	_	20	
Output enable time	t _{pZL}	Figure	1 (Note 1)	GND	3.0		5.7	9.0	_	11	ns
Output enable time	t _p ZH	riguie	(140(6-1)	GND	4.5		4.5	6.0	_	7.0	
				-3.0	3.0		5.8	8.0	_	10	
				GND	2.0		13.5	21	_	25	ns
Output disable time	t _{pLZ} t _{pHZ}	Figure 1 (Note 1)	1 (Note 1)	GND	3.0		11.3	15	_	18	
Output disable lime			GND	4.5		10.3	12	_	14	113	
				-3.0	3.0		10.9	13	_	15	
Control input capacitance	Cin	All type	es (Note 2)	_	_	_	5	10	_	10	pF
	C _{IS}	4051	Figure 2 (Note 2)			_	11	25		25	
COMMON terminal capacitance		4052		-3.0	3.0		9 2	20	_	20	pF
·		4053					7	15		15	
		4051 Figure 2				6	13		13		
SWITCH terminal capacitance	Cos	4052	(Note 2)	-3.0	3.0	_	6	13	_	13	pF
		4053	(14010 2)				6	13		13	
		4051			-3.0 3.0		3	6		6	
Feedthrough capacitance	C _{IOS}	4052	Figure 2 (Note 2)	-3.0		_	3	6	_	6	pF
		4053	, ,				3	6		6	
		4051				14					
Power dissipation capacitance	C_PD	4052	Figure 2 (Note 3)	GND	6.0	_	24	_		_	pF
		4053	,				18				

Note1: $R_L = 1 k\Omega$

Note2: C_{in} , C_{IS} , C_{OS} and C_{IOS} are guaranteed by the design.

Note3: CPD is defined as the value of the internal equivalent capacitance of IC which is calculated from the

operating current consumption without load.

Average operating current can be obtained by the equation:

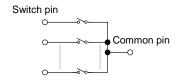
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$



*Analog Switch Characteristics (GND = 0 V, Ta = 25°C)

Characteristics	Symbol	Test Condition			Тур.	Unit	
Characteristics	Cymbol	rest condition		V _{EE} (V) V _{CC} (V)			
			$V_{IN} = 2.0 V_{p-p}$	0	3.0	0.100	
Sine Wave Distortion (T.H.D)		$R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF},$ $f_{IN} = 1 \text{ kHz}$	$V_{IN} = 4.0 V_{p-p}$	0	4.5	0.030	%
			$V_{IN} = 6.0 V_{p-p}$	-0.3	3.0	0.020	
			4051			150	MHz
			4052	0	3.0	180	
		Adjust f _{IN} voltage to obtain 0dBm at V _{OS}	4053			200	
Eroguanay raananaa		Increase f _{IN} frequency until dB	4051			150	
Frequency response (switch ON)	f _{max}	meter reads –3dB.	4052	0	4.5	180	
(SWILCH ON)		$R_L = 50 \Omega$, $C_L = 10 pF$, $f_{IN} = 1 MHz$, sine wave	4053			200	
		Figure 3	4051		3.0	150	
			4052	-3.0		180	
			4053			200	
		V _{IN} is centered at (V _{CC} – V _{EE})/2.	0	3.0	-45	dB	
		Adjust input for 0dBm.	0	4.5	-45		
		$R_L = 600 \Omega$, $C_L = 50 pF$, $f_{IN} = 1 M$	- 0	4.5	-4 5		
Feed through attenuation (switch OFF)		Figure 4	-3.0	3.0	−45		
,				0	3.0	-60	
		$R_L = 50 \Omega$, $C_L = 10 pF$, $f_{IN} = 1 MH$	0	4.5	-60		
			-3.0	3.0	-60		
Crosstalk		$R_L = 600 \Omega$, $C_L = 50 pF$, $f_{IN} = 1 M$	Hz, square wave	0	3.0	90	
(control input to signal		$(t_{\Gamma}=t_{f}=6 \text{ ns})$	0	4.5	150	mV	
output)		Figure 5	-3.0	3.0	120		
Croostalle		Adjust V _{IN} to obtain 0dBm at input	0	3.0	-45	dB	
Crosstalk		$R_L = 600 \Omega$, $C_L = 50 pF$, $f_{IN} = 1 M$	0	4.5	-45		
(between any switches)		Figure 6	Figure 6			-45	

*: These characteristics are determined by design of devices.



AC Test Circuit

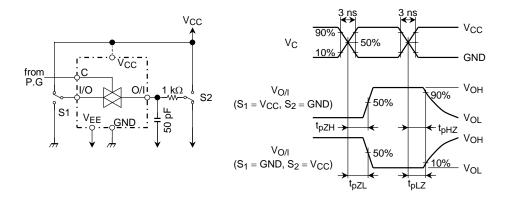


Figure 1 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

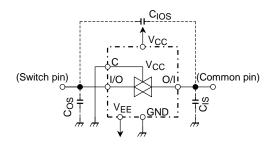


Figure 2 C_{IOS}, C_{IS}, C_{OS}

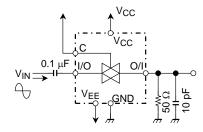


Figure 3 Frequency Response (switch on)

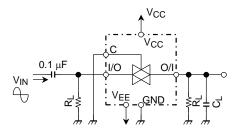


Figure 4 Feedthrough

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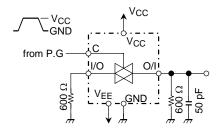


Figure 5 Cross Talk (control input to output signal)

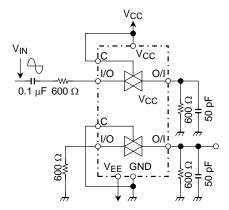
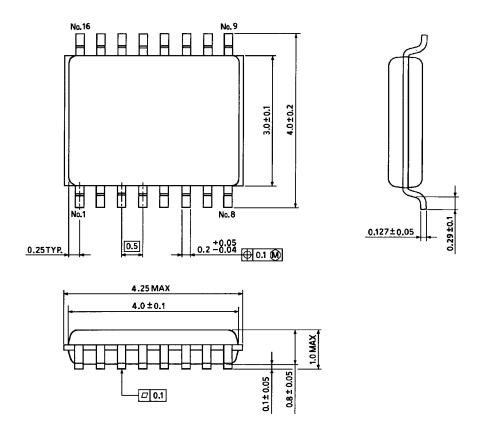


Figure 6 Cross Talk (between any two switches)

Package Dimensions



Weight: 0.02 g (typ.)

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000707EBA

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